MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ CE

600V CoolMOS™ CE Power Transistor
IPX60R2K1CE

Data Sheet

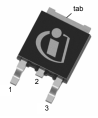
Rev. 2.1
Final

Power Management & Multimarket

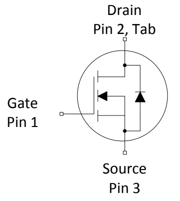
1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ CE is a price-performance optimized platform enabling to target cost sensitive applications in Consumer and Lighting markets by still meeting highest efficiency standards. The new series provides all benefits of a fast switching Superjunction MOSFET while not sacrificing ease of use and offering the best cost down performance ratio available on the market.

DPAK



IPAK



Features

- Extremely low losses due to very low FOM Rdson*Qg and Eoss
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for standard grade applications

Applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV and indoor lighting.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	650	V
$R_{DS(on),max}$	2100	mΩ
$Q_{g.typ}$	6.7	nC
$I_{D,pulse}$	6	A
E_{oss}@400V	0.76	µJ
Body diode di/dt	500	A/µs

Type / Ordering Code	Package	Marking	Related Links
IPD60R2K1CE	PG-TO 252	60S2K1CE	see Appendix A
IPU60R2K1CE	PG-TO 251		

Table of Contents

2 Maximum ratings

at T_j = 25°C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1)]	I_D	- -	- -	2.3 1.5	A	T_C=25°C T_C=100°C
Pulsed drain current[2)]	$I_{D,pulse}$	-	-	6	A	T_C=25°C
Avalanche energy, single pulse	E_{AS}	-	-	11	mJ	I_D=0.4A; V_{DD}=50V; see table 11
Avalanche energy, repetitive	E_{AR}	-	-	0.06	mJ	I_D=0.4A; V_{DD}=50V; see table 11
Avalanche current, repetitive	I_{AR}	-	-	0.4	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	V_{DS}=0...480V
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC (f>1 Hz)
Power dissipation TO-252, TO-251	P_{tot}	-	-	22	W	T_C=25°C
Storage temperature	T_{stg}	-40	-	150	°C	-
Operating junction temperature	T_j	-40	-	150	°C	-
Continuous diode forward current	I_S	-	-	2.0	A	T_C=25°C
Diode pulse current[2)]	$I_{S,pulse}$	-	-	6	A	T_C=25°C
Reverse diode dv/dt[3)]	dv/dt	-	-	15	V/ns	V_{DS}=0...400V, I_{SD}<=I_S, T_j=25°C see table 9
Maximum diode commutation speed	di_f/dt	-	-	500	A/µs	V_{DS}=0...400V, I_{SD}<=I_S, T_j=25°C see table 9

1) Limited by $T_{j\,max}$. Maximum duty cycle D=0.75
2) Pulse width t_p limited by $T_{j,max}$
3) Identical low side and high side switch with identical R_G

3 Thermal characteristics

Table 3 Thermal characteristics TO-251

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	5.6	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

Table 4 Thermal characteristics TO-252

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	5.6	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	35	45	°C/W	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling.
Soldering temperature, wave & reflow soldering allowed	T_{sold}	-	-	260	°C	reflow MSL1

4 Electrical characteristics

at T_j=25°C, unless otherwise specified

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	V_{GS}=0V, I_D=0.25mA
Gate threshold voltage	$V_{(GS)th}$	2.5	3.0	3.5	V	V_{DS}=V_{GS}, I_D=0.06mA
Zero gate voltage drain current	I_{DSS}	- -	- 10	1 -	µA	V_{DS}=600, V_{GS}=0V, T_j=25°C V_{DS}=600, V_{GS}=0V, T_j=150°C
Gate-source leakage current	I_{GSS}	-	-	100	nA	V_{GS}=20V, V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	- -	1.80 4.68	2.10 -	Ω	V_{GS}=10V, I_D=0.76A, T_j=25°C V_{GS}=10V, I_D=0.76A, T_j=150°C
Gate resistance	R_G	-	12	-	Ω	f=1MHz, open drain

Table 6 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	140	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Output capacitance	C_{oss}	-	12	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Effective output capacitance, energy related[1]	$C_{o(er)}$	-	8.5	-	pF	V_{GS}=0V, V_{DS}=0...480V
Effective output capacitance, time related[2]	$C_{o(tr)}$	-	30	-	pF	I_D=constant, V_{GS}=0V, V_{DS}=0...480V
Turn-on delay time	$t_{d(on)}$	-	7	-	ns	V_{DD}=400V, V_{GS}=10V, I_D=0.9A, R_G=12.2Ω; see table 10
Rise time	t_r	-	7	-	ns	V_{DD}=400V, V_{GS}=10V, I_D=0.9A, R_G=12.2Ω; see table 10
Turn-off delay time	$t_{d(off)}$	-	30	-	ns	V_{DD}=400V, V_{GS}=10V, I_D=0.9A, R_G=12.2Ω; see table 10
Fall time	t_f	-	50	-	ns	V_{DD}=400V, V_{GS}=10 V, I_D=0.9A, R_G=12.2Ω; see table 10

Table 7 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	0.8	-	nC	V_{DD}=480V, I_D=0.9A, V_{GS}=0 to 10V
Gate to drain charge	Q_{gd}	-	3.6	-	nC	V_{DD}=480V, I_D=0.9A, V_{GS}=0 to 10V
Gate charge total	Q_g	-	6.7	-	nC	V_{DD}=480V, I_D=0.9A, V_{GS}=0 to 10V
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	V_{DD}=480V, I_D=0.9A, V_{GS}=0 to 10V

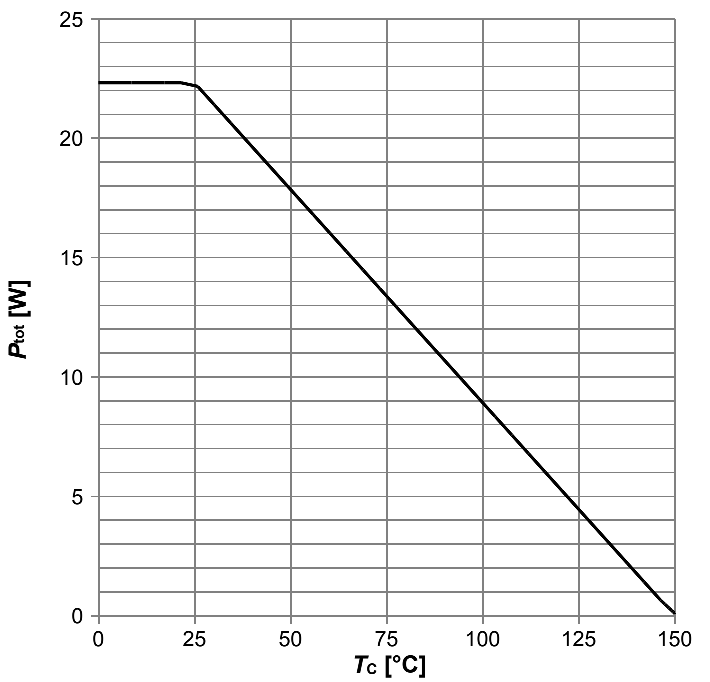
[1] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{o(BR)DSS}$
[2] $C_{o(tr)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{o(BR)DSS}$

Table 8 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	V_{GS}=0V, I_F=0.9A, T_j=25°C
Reverse recovery time	t_{rr}	-	180	-	ns	V_R=400V, I_F=0.9A, di_F/dt=100A/µs; see table 9
Reverse recovery charge	Q_{rr}	-	0.67	-	µC	V_R=400V, I_F=0.9A, di_F/dt=100A/µs; see table 9
Peak reverse recovery current	I_{rrm}	-	7.1	-	A	V_R=400V, I_F=0.9A, di_F/dt=100A/µs; see table 9

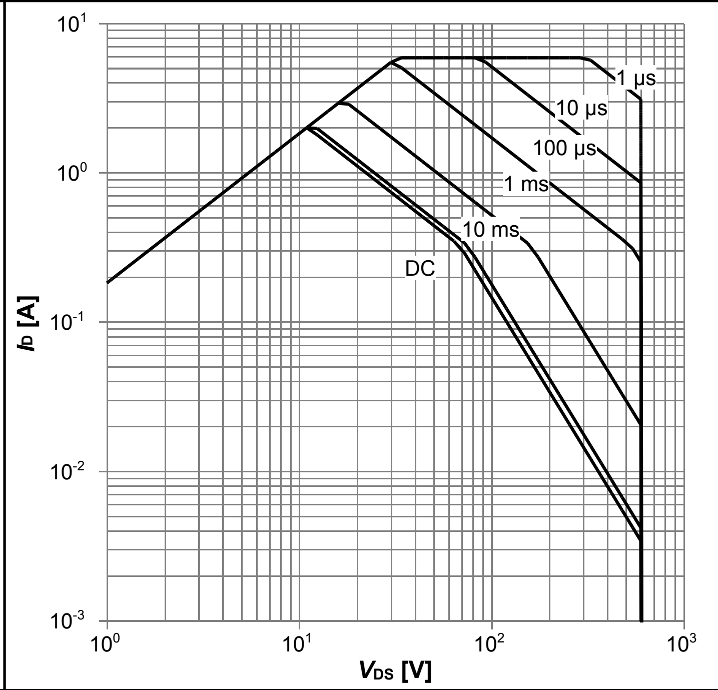
5 Electrical characteristics diagrams

Diagram 1: Power dissipation



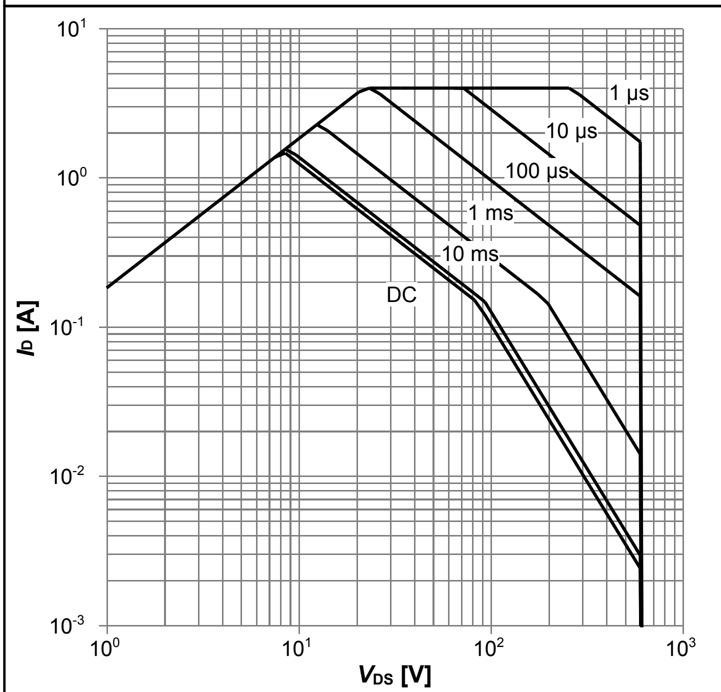
P_{tot}=f(T_C)

Diagram 2: Safe operating area



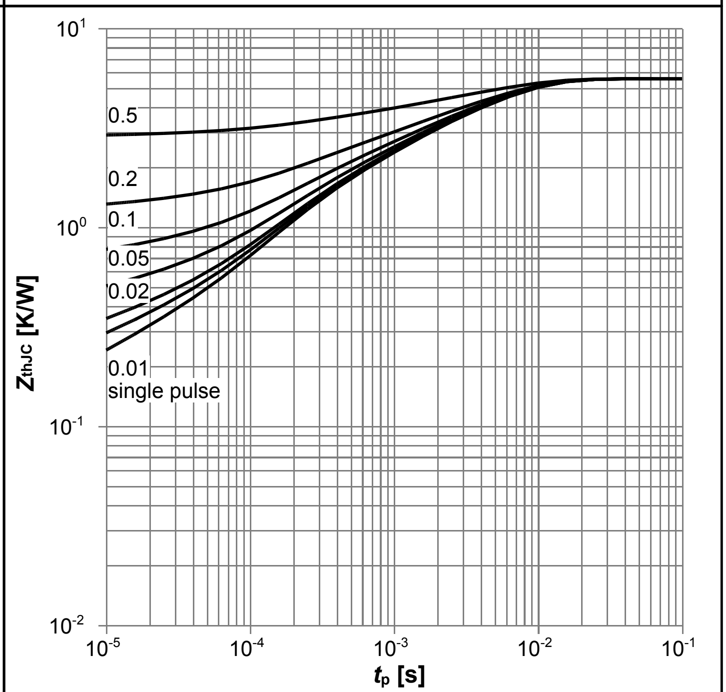
I_D=f(V_{DS}); T_C=25 °C; D=0; parameter: t_p

Diagram 3: Safe operating area



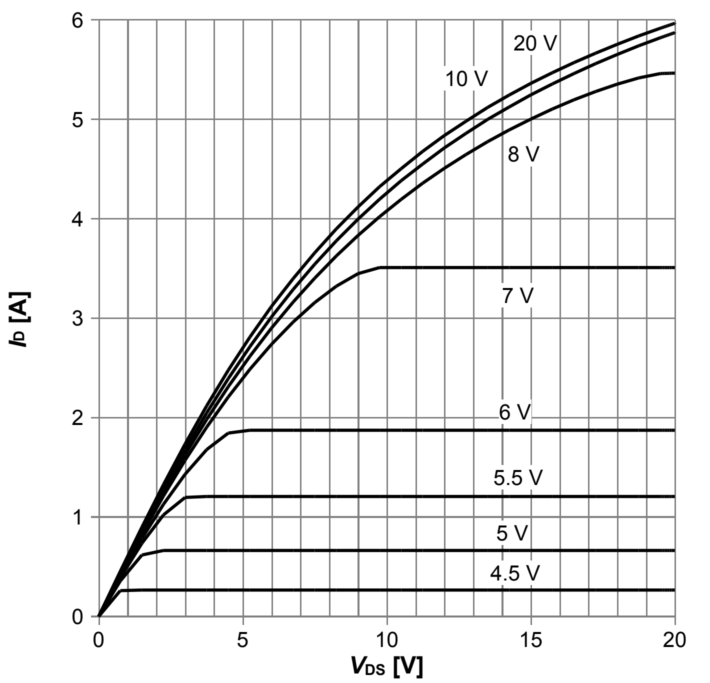
I_D=f(V_{DS}); T_C=80 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



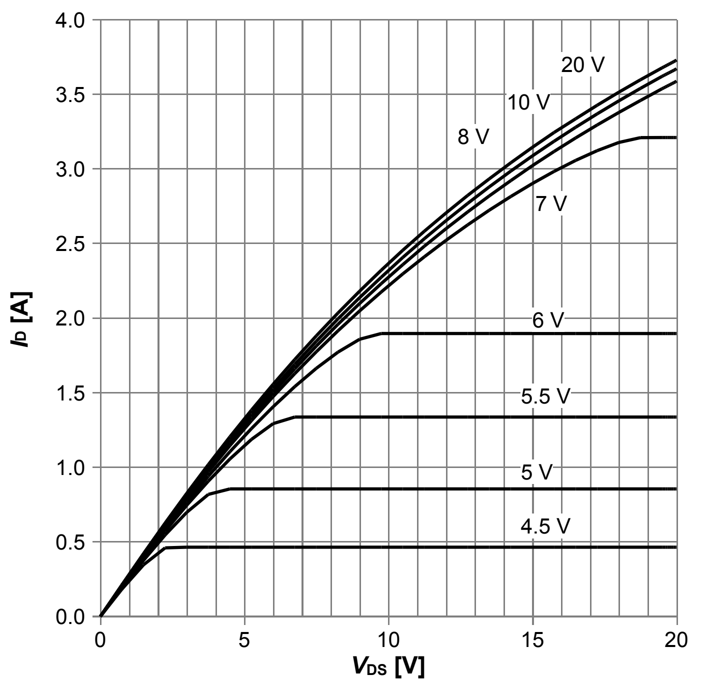
Z_{thJC} =f(t_P); parameter: D=t_p/T

Diagram 5: Typ. output characteristics



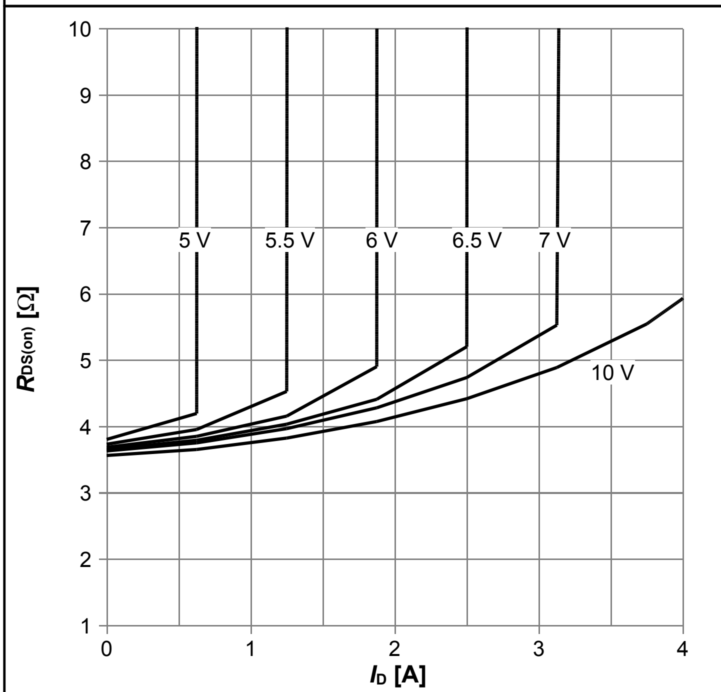
I_D=f(V_{DS}); T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. output characteristics



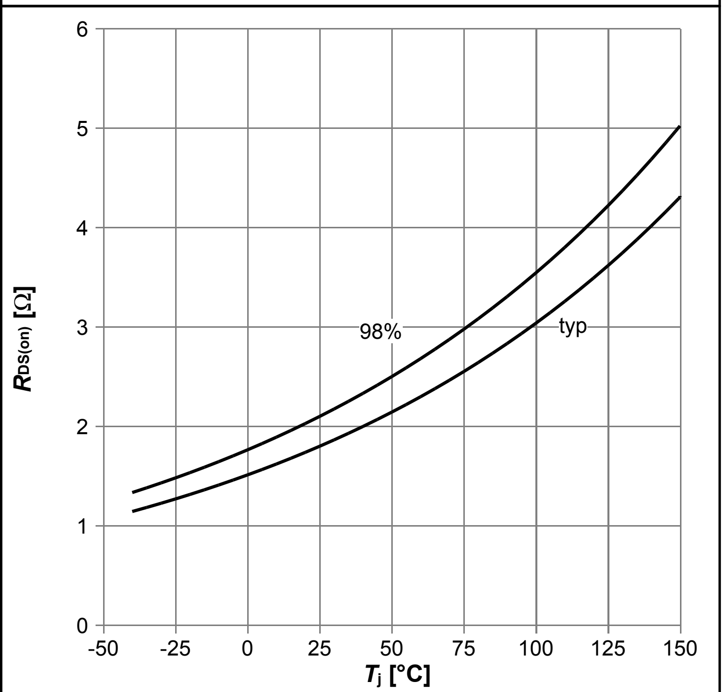
I_D=f(V_{DS}); T_j=125 °C; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



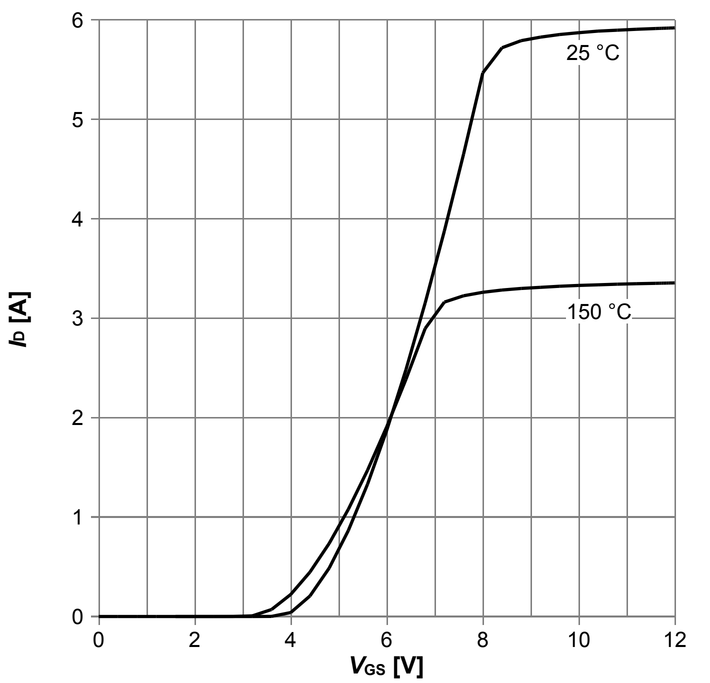
$R_{DS(on)}$=f(I_D); T_j=125 °C; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



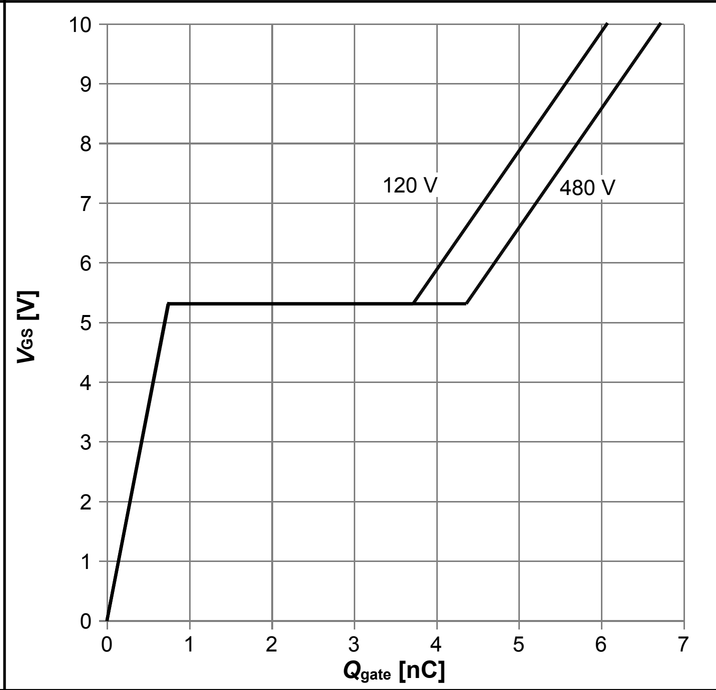
$R_{DS(on)}$=f(T_j); I_D=0.76 A; V_{GS}=10 V

Diagram 9: Typ. transfer characteristics



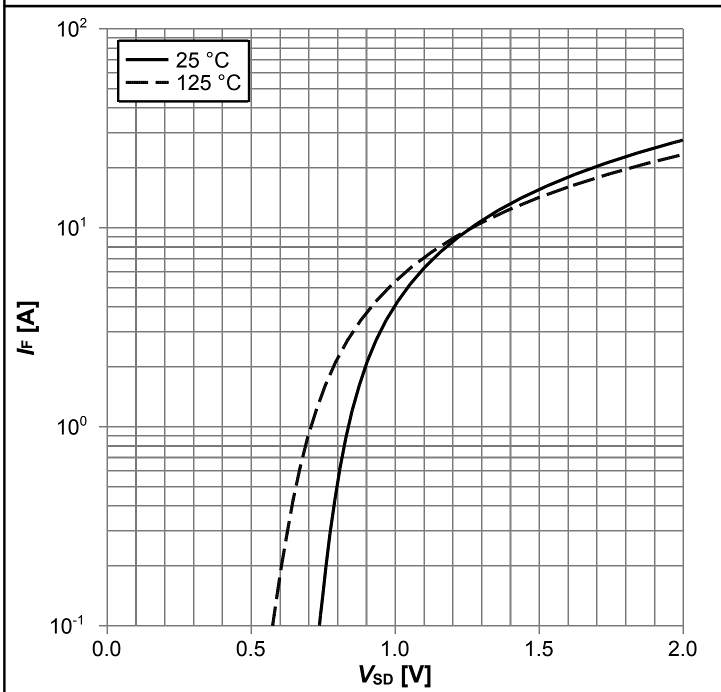
I_D=f(V_{GS}); V_{DS}=20V; parameter: T_j

Diagram 10: Typ. gate charge



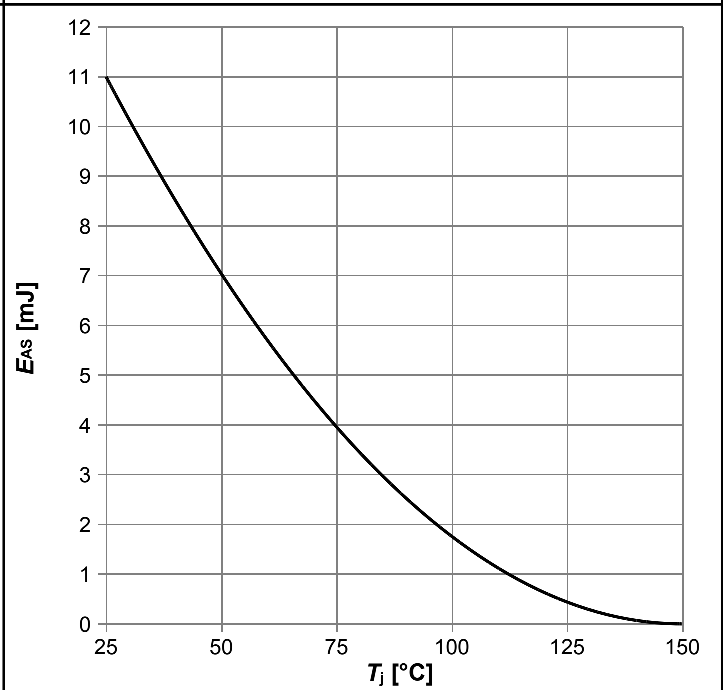
V_{GS}=f(Q_{gate}); I_D=0.9 A pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



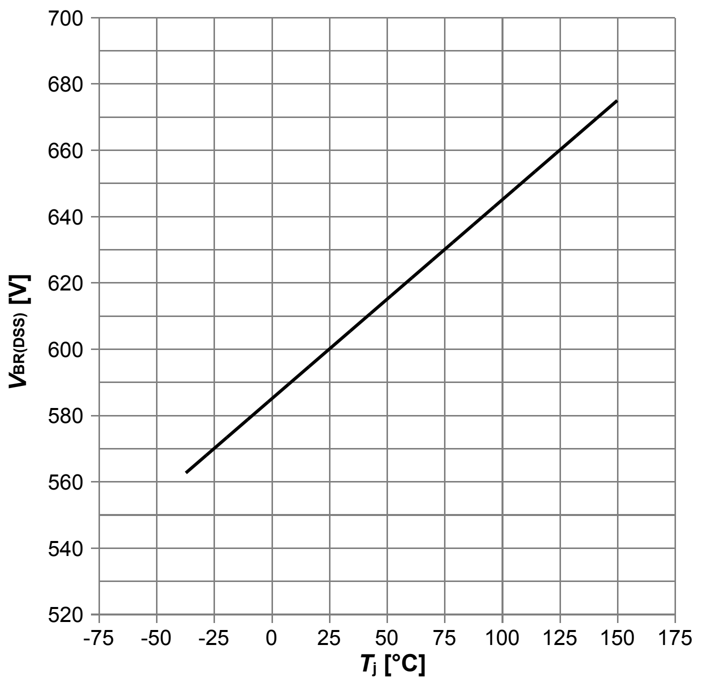
I_F=f(V_{SD}); parameter: T_j

Diagram 12: Avalanche energy



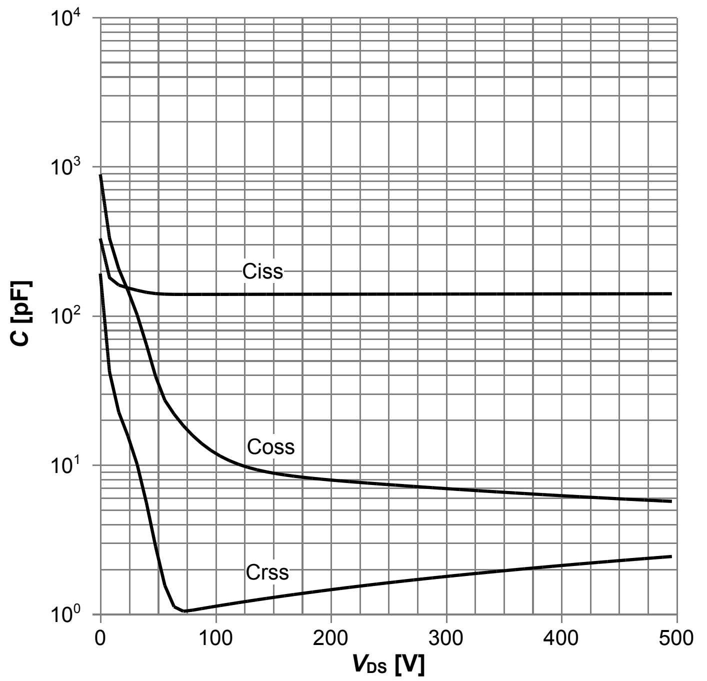
E_{AS}=f(T_j); I_D=0.4 A; V_{DD}=50 V

Diagram 13: Drain-source breakdown voltage



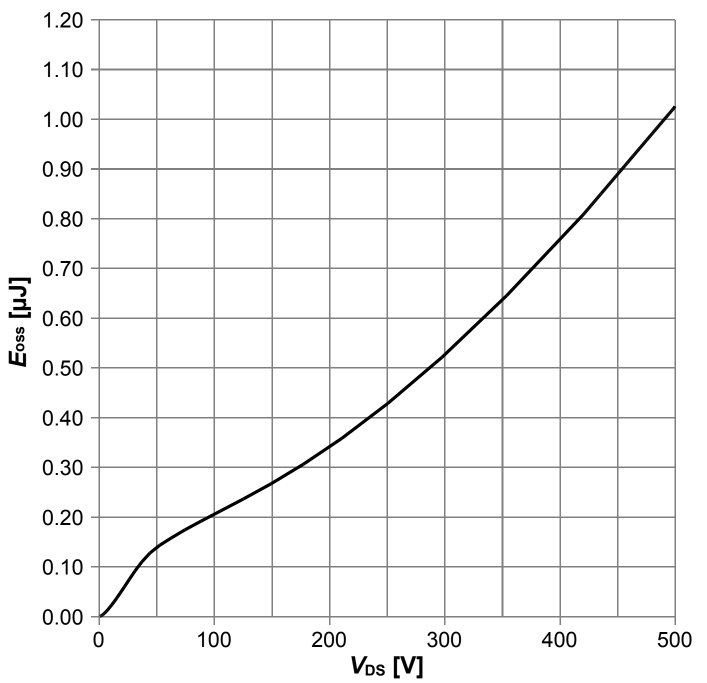
$V_{BR(DSS)}$=f(T_j); I_D=0.25 mA

Diagram 14: Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 15: Typ. Coss stored energy



E_{oss}=f(V_{DS})

6 Test Circuits

Table 9 Diode characteristics

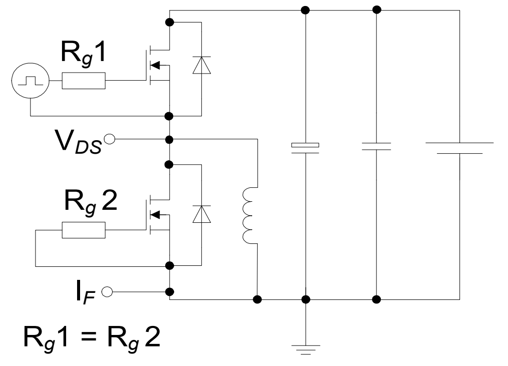
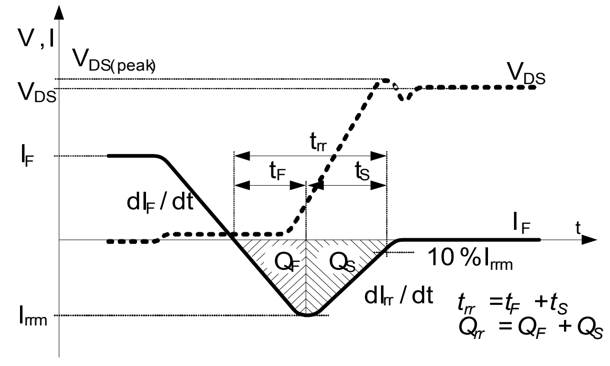
<table>
<tr><th>Test circuit for diode characteristics</th><th>Diode recovery waveform</th></tr>
<tr><td>
</td><td>
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Table 10 Switching times

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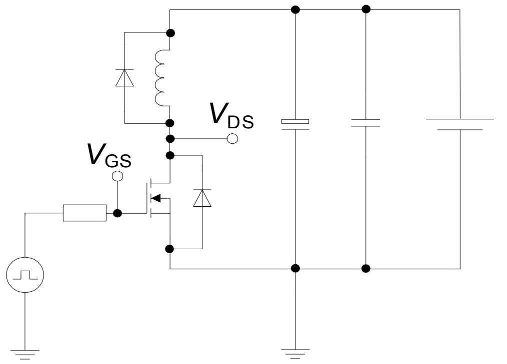
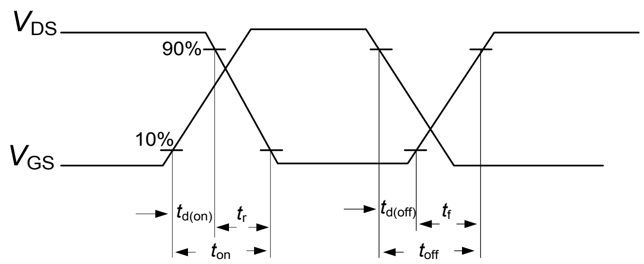
<tr><th>Switching times test circuit for inductive load</th><th>Switching times waveform</th></tr>
<tr><td>
</td><td>
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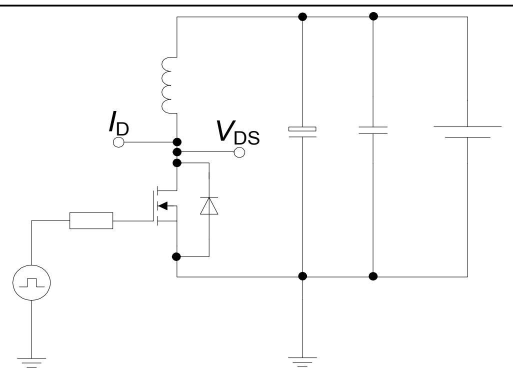
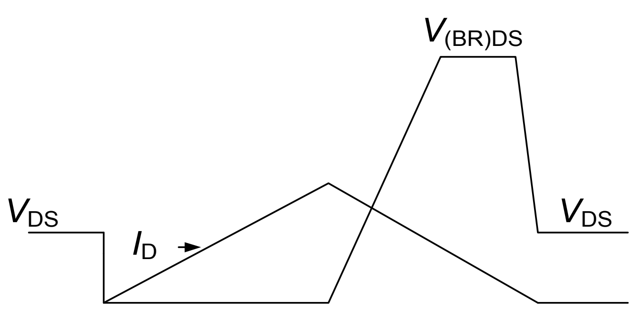
Table 11 Unclamped inductive load

<table>
<tr><th>Unclamped inductive load test circuit</th><th>Unclamped inductive waveform</th></tr>
<tr><td>
</td><td>
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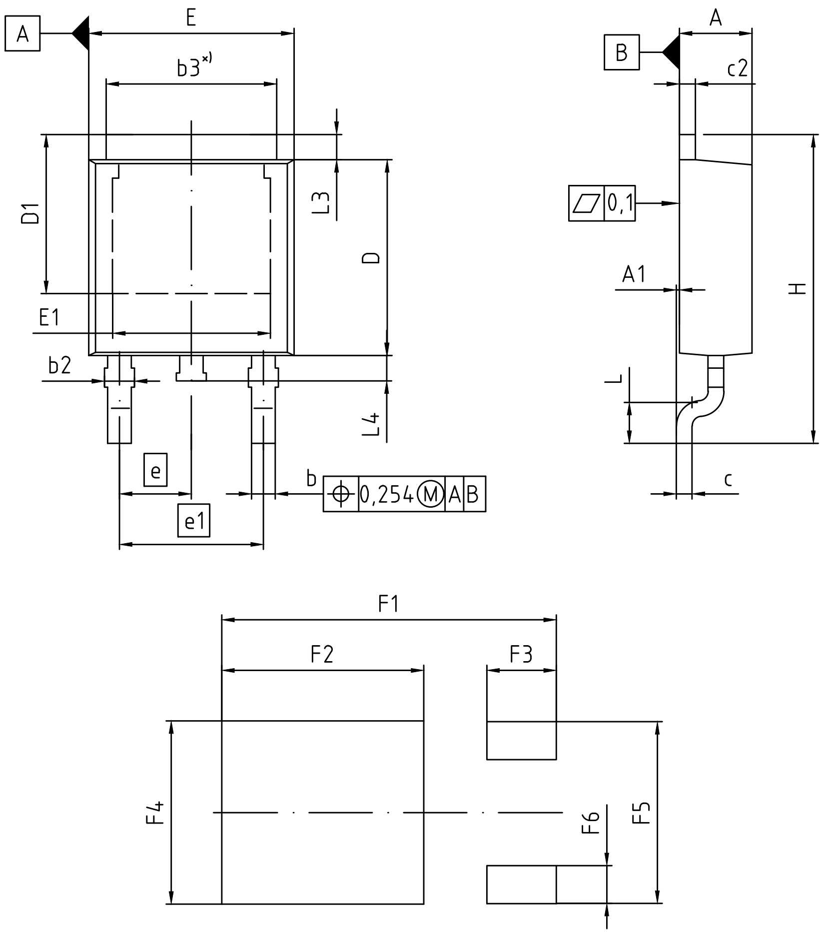
7 Package Outlines



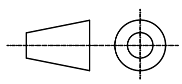
*) mold flash not included

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.60	0.185	0.220
e	2.29 (BSC)		0.090 (BSC)	
e1	4.57 (BSC)		0.180 (BSC)	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.60		0.417	
F2	6.40		0.252	
F3	2.20		0.087	
F4	5.80		0.228	
F5	5.76		0.227	
F6	1.20		0.047	

DOCUMENT NO.
Z8B00003328

SCALE 0 2.0 4mm

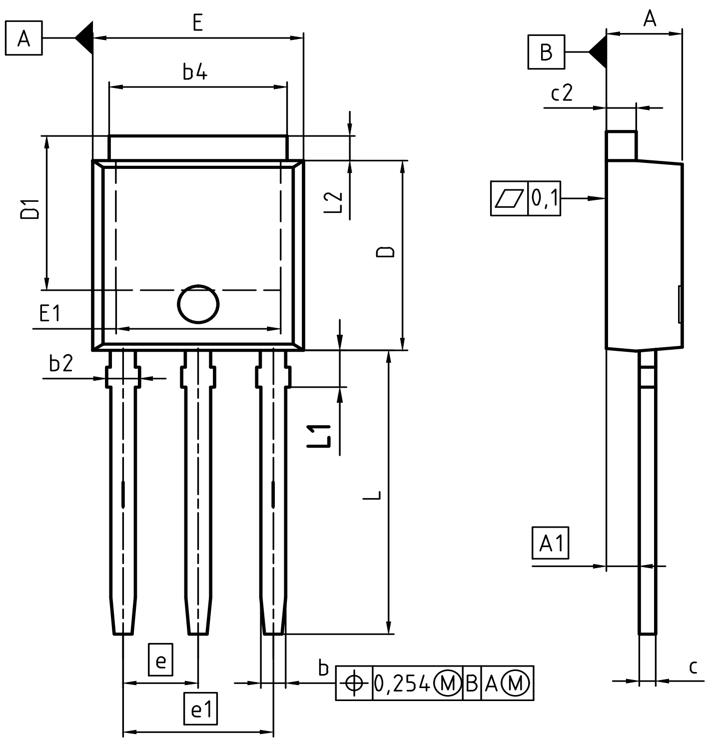
EUROPEAN PROJECTION



ISSUE DATE
01-09-2015

REVISION
05

Figure 1 Outline PG-TO 252, dimensions in mm/inches

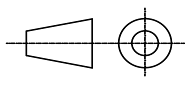


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.90	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.77	0.198	0.227
E	6.35	6.73	0.250	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	8.89	9.65	0.350	0.380
L1	0.85	2.29	0.033	0.090
L2	0.89	1.37	0.035	0.054

DOCUMENT NO.
Z8B00003330

SCALE 0 2.0 4mm

EUROPEAN PROJECTION



ISSUE DATE
31-08-2015

REVISION
04

Figure 2 Outline PG-TO 251, dimensions in mm/inches

8 Appendix A

Table 12 Related Links

- **IFX CoolMOS™ CE Webpage:** www.infineon.com
- **IFX CoolMOS™ CE application note:** www.infineon.com
- **IFX CoolMOS™ CE simulation model:** www.infineon.com
- **IFX Design tools:** www.infineon.com

Revision History

IPD60R2K1CE, IPU60R2K1CE

Revision: 2015-11-17, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2014-09-25	Release of final version
2.1	2015-11-17	Updated with qualified for standard grade & updated package drawing

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The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.